DESCRIPTION

AM3423 is available in a SOT-23S package.

FEATURES

- -20V/-2A,
  $R_{DS(ON)}$ = 150mΩ(MAX) @V_{GS} = -4.5V
  $R_{DS(ON)}$ = 180mΩ(MAX) @V_{GS} = -2.5V
- Super High dense cell design for extremely low $R_{DS(ON)}$
- Reliable and Rugged
- Available in a SOT-23S package.

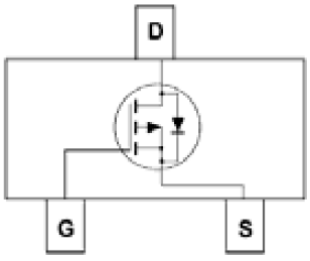
ORDERING INFORMATION

Package Type	Part Number	
SOT-23S SPQ: 3,000pcs/Reel	E3S	AM3423E3SR
		AM3423E3SVR
Note	V: Halogen free Package R: Tape & Reel	
AiT provides all RoHS products		

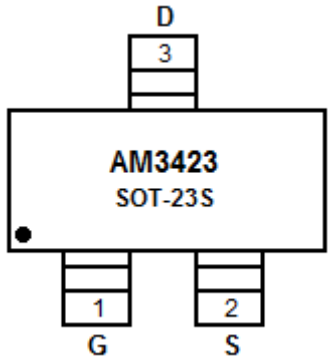
APPLICATION

- Power Management
- Portable Equipment and Battery Powered Systems

PIN DESCRIPTION



PIN DESCRIPTION



Top View

Pin #	Symbol	Function
1	G	Gate
2	S	Source
3	D	Drain

ABSOLUTE MAXIMUM RATINGS

T_C= 25℃, unless otherwise noted

V_{DS}, Drain-Source Voltage	-20V
V_{GS}, Gate-Source Voltage	±10V
I_D, Drain Current-Continuous	-2A

Stress beyond above listed “Absolute Maximum Ratings” may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

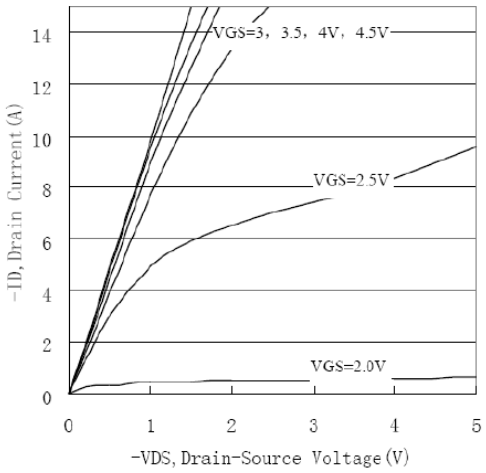
ELECTRICAL CHARACTERISTICS

T_A = 25℃, unless otherwise noted

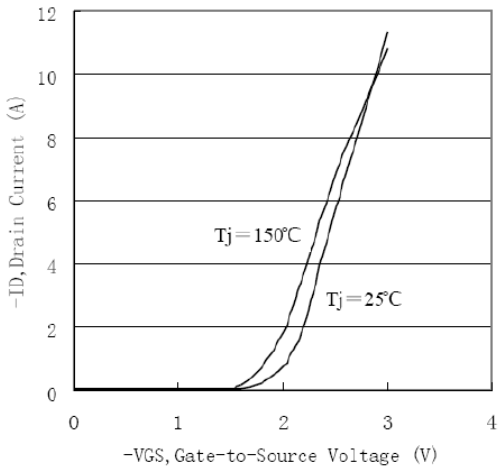
Parameter	Symbol	Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=-250μA	-20	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current, Forward	I_{GSSF}	V_{GS}=10V, V_{DS}=0V	-	-	100	nA
Gate-Body Leakage Current, Reverse	I_{GSSR}	V_{GS}=-10V, V_{DS}=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS},I_D=-250μA	-0.4	-	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V,I_D=-3.0A	-	-	150	mΩ
		V_{GS}=-2.5V,I_D=-2.0A	-	-	180	
Drain-Source Diode Characteristics and Maximum Ratings						
Diode-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=1.25A	-	-	-1.2	V

TYPICAL CHARACTERISTICS

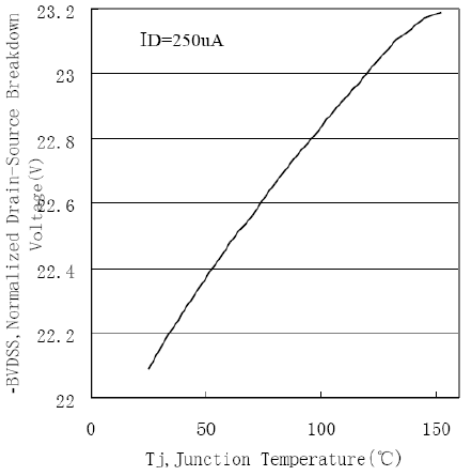
1. Output Characteristics



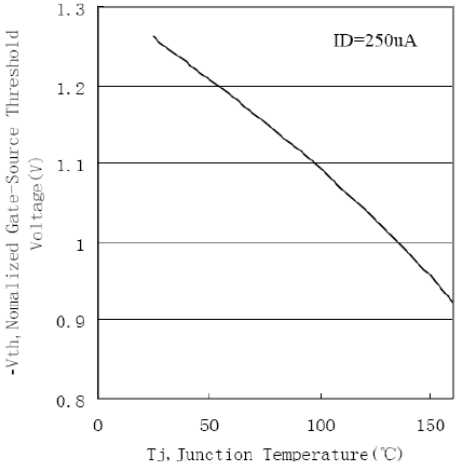
2. Transfer Characteristics



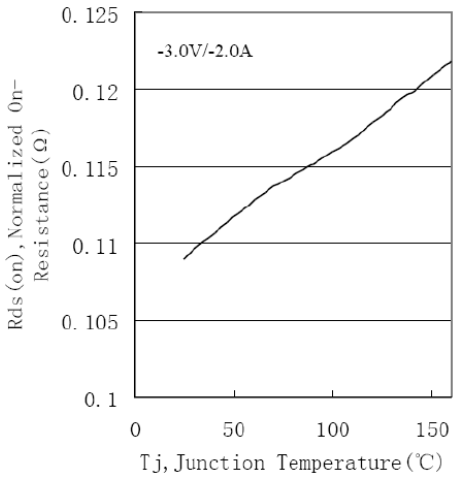
3. Breakdown Voltage Variation with Temperature



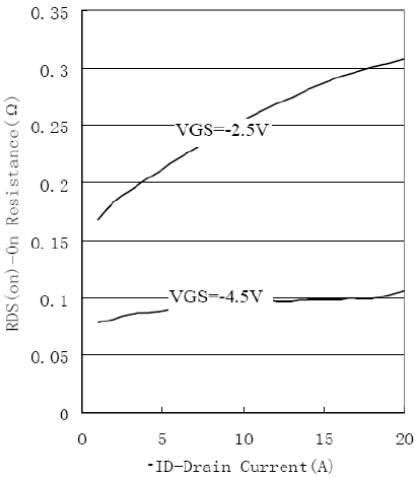
4. Gate Threshold Variation with Temperature



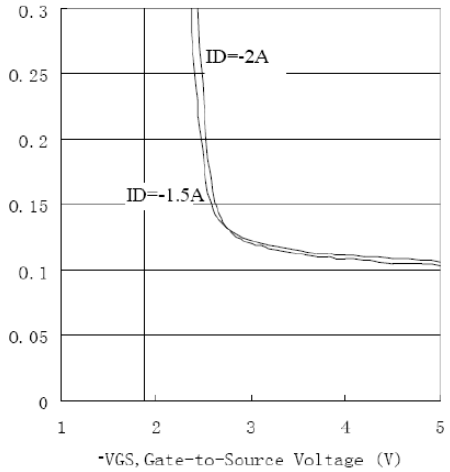
5. On-Resistance Variation with Temperature



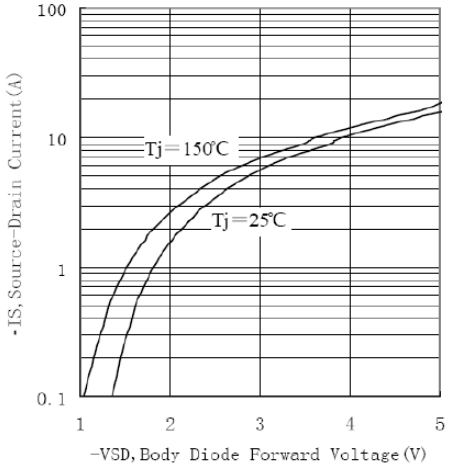
6. On-Resistance vs. Drain Current



7. On-Resistance vs. Gate-to-Source Voltage

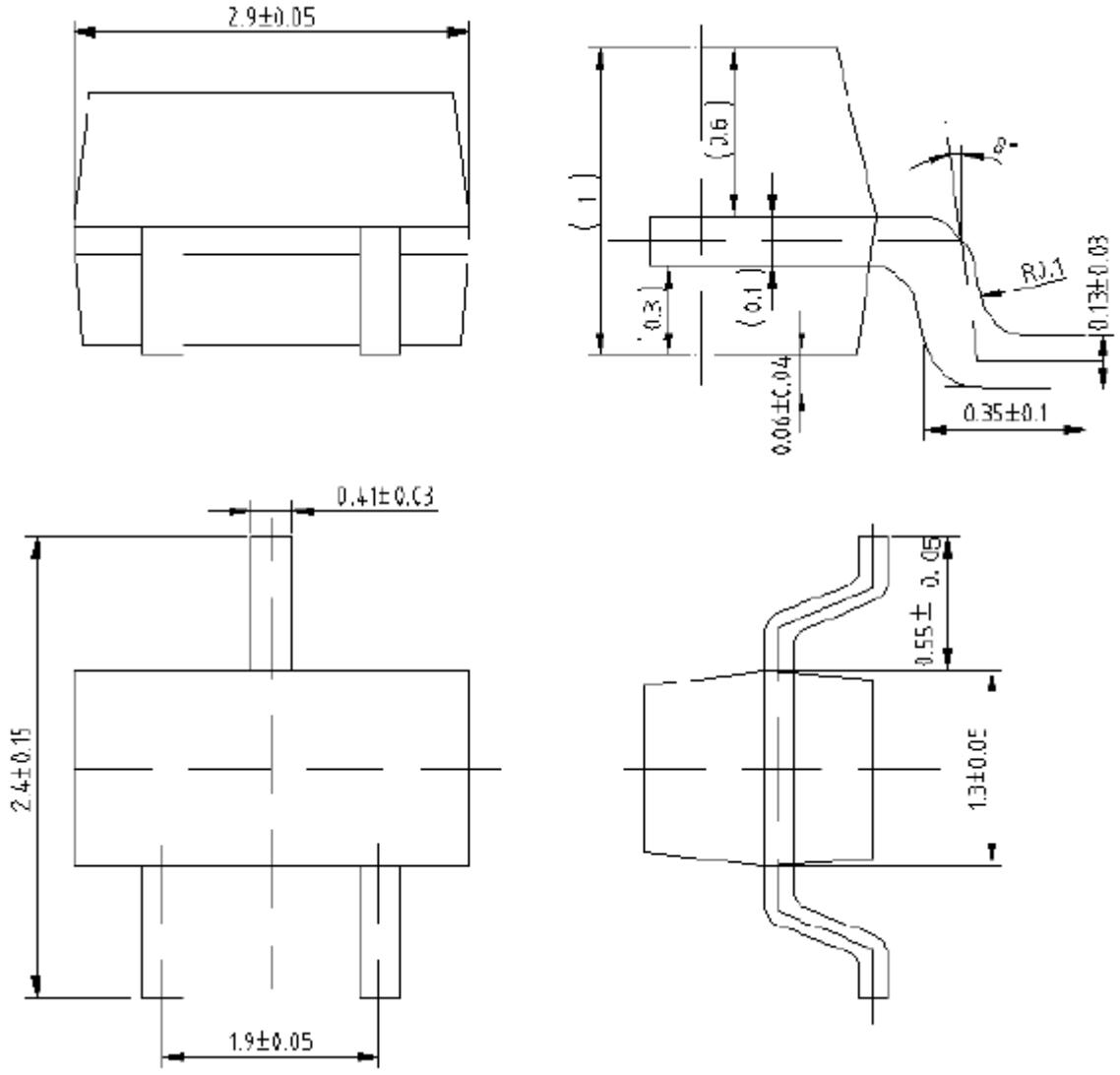


8. Source-Drain Diode Forward Voltage



PACKAGE INFORMATION

Dimension in SOT-23S (Unit: mm)



IMPORTANT NOTICE

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